

LPCVD	Tube 2	Material	Phosphorous Doped Poly Silicon Crystalline	
Uniformity:	Film Uniformity Variance < 2% to 5% across 4" wafer			
Gases	Flow Rate	Time (minutes)	Film Thickness (nm)	Deposition rate (nm/min)
Temperature	620 C	10	54.7	5.47
Comments: With Wet Etch step height for 50 min sample is 291.6 nm and Dep. Rate is 5.83 nm/min		20	111.5	5.58
		30	186.4	6.21
		40	277	6.93
		50	318.3	6.37
		60	345.4	5.76

